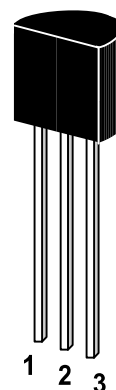


ST 2SC1740

NPN Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into four groups Q, R, S
and E. according to its DC current gain.

On special request, these transistors can be
manufactured in different pin configurations.



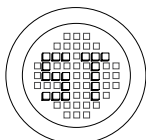
1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25°)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	60	V
Collector Emitter Voltage	V _{CEO}	50	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	I _C	150	mA
Power Dissipation	P _{tot}	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _s	-55 to +150	°C

G S P FORM A IS AVAILABLE



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РАДИОТЕХ-ТРЕЙД

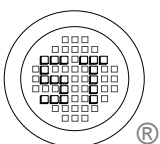
Тел.: (495) 795-0805
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Эл. почта: info@rct.ru
Веб: www.rct.ru

ST 2SC1740

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

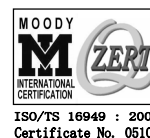
	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE}=6\text{V}$, $I_C=1\text{mA}$	Q	h_{FE}	120	-	270	-
	R	h_{FE}	180	-	390	-
	S	h_{FE}	270	-	560	-
	E	h_{FE}	390	-	820	-
Collector Base Breakdown Voltage at $I_C=50\mu\text{A}$	$V_{(BR)CBO}$	60	-	-	V	
Collector Emitter Breakdown Voltage at $I_C=1\text{mA}$	$V_{(BR)CEO}$	50	-	-	V	
Emitter Base Breakdown Voltage at $I_E=50\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V	
Collector Cutoff Current at $V_{CB}=60\text{V}$	I_{CBO}	-	-	0.1	μA	
Emitter Cutoff Current at $V_{EB}=5\text{V}$	I_{EBO}	-	-	0.1	μA	
Collector Saturation Voltage at $I_C=50\text{mA}$, $I_B=5\text{mA}$	$V_{CE(sat)}$	-	-	0.4	V	
Gain Bandwidth Product at $V_{CE}=12\text{V}$, $I_C=2\text{mA}$	f_T	-	180	-	MHz	
Output Capacitance at $V_{CB}=12\text{V}$, $f=1\text{MHz}$	C_{OB}	-	2	3.5	pF	

G S P FORM A IS AVAILABLE



SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, acompany listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 07/12/2002